

S.N. 09/612,260

Amendment Under 37 CFR 1.111

Sub C¹

- B*
- 1 1. (Amended) A transistor comprising:
2 a channel region;
3 a first gate on top of said channel region;
4 a second gate below said channel region; and
5 an isolation layer below said second gate,
6 wherein said first gate and said second gate are electrically separated from each other.

Sub C²

- B²*
- 1 11. (Amended) A semiconductor chip having at least one transistor, said transistor
2 comprising:
3 a channel region;
4 a first gate on top of said channel region;
5 a second gate below said channel region; and
6 an isolation layer below said second gate,
7 wherein said first gate comprises a different material than said second gate.